

MJ11017 PNP SILICON DARLINGTON TRANSISTOR

**SWITCHING REGULATORS PWM INVERTERS
SOLENOID AND RELAY DRIVERS**

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	-150	V
Collector-Emitter Voltage	VCEO	-150	V
Collector Current (DC)	IC	-15	A
Collector Dissipation ($T_c=25^{\circ}\text{C}$)	PC	200	W
Junction Temperature	Tj	200	$^{\circ}\text{C}$
Storage Temperature	Tstg	-50~150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	ICBO	VCB=-150V, IE=0			10	μA
Collector Cutoff Current	ICEO	VCB=-150V, IB=0			10	μA
DC Current Gain	hFE	VCE=-5V, IC=-10A	1K			
Collector- Emitter Saturation Voltage	VCE(sat)	IC=-6A, IB=-0.6A			-1.5	V

NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

Quality Semi-Conductors



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.550	REF	39.37	REF
B	—	1.050	—	26.67
C	0.250	0.335	6.35	8.51
D	0.036	0.043	0.97	1.08
E	0.055	0.070	1.40	1.77
G	0.430	BSC	10.92	BSC
H	0.215	BSC	5.46	BSC
K	0.440	0.480	11.18	12.19
L	0.665	BSC	16.88	BSC
N	—	0.630	—	21.08
Q	0.151	0.165	3.84	4.19
U	1.187	BSC	30.15	BSC
V	0.131	0.168	3.33	4.27

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR